C. Material Growth & Characterization 분과

2021년 1월 28일(목), 09:00–10:30 / 채널 B

[TB1-C] Wide Bandgap Materials I

좌장: 김지현 교수 (고려대학교), 이신범 교수 (DGIST)

TB1-C-1 **09:00-09:30**	[초청] **Bulk-Rashba Effect in the Non-Centrosymmetric Artificial Superlattice** Sanghoon Kim *Department of Physics, University of Ulsan*
TB1-C-2 **09:30-09:45**	**Diamond Schottky Barrier Diode Grown on Sapphire-based Freestanding Heteroepitaxial Diamond Substrate Using Microwave Plasma Chemical Vapor Deposition** Taemyung Kwak[1], Uiho Choi[1], Jonggun Lee[1], Sanghun Han[1], Geunho Yoo[1], Seong-woo Kim[2], and Okhyun Nam[1] *[1]Department of Nano & Semiconductor Engineering, Korea Polytechnic University,* *[2]Namiki Precision Jewel Co., Ltd.*
TB1-C-3 **09:45-10:00**	**Boron-doped Diamond Metal-semiconductor Field-effect Transistor Grown on Hetero-epitaxial Diamond Substrate** Uiho Choi[1], Taemyung Kwak[1], Jonggun Lee[1], Sanghun Han[1], Geunho Yoo[1] Seongwoo Kim[2], and Okhyun Nam[1] *[1]Convergence Center for Advanced Nano Semiconductor, Department of Nano & Semiconductor Engineering, Korea Polytechnic University, [2]Adamant Namiki Precision Jewel Co., Ltd.*
TB1-C-4 **10:00-10:15**	**Effect of Doping on the Threading Dislocation Density of GaAs Layer Epitaxially Grown on Si** Geunhwan Ryu[1], Seungwan Woo[1,2], Rafael Chu[1], In-Hwan Lee[2], Daehwan Jung[1], and Won Jun Choi[1] *[1]Center for Opto-electronic Materials and Devices, KIST,* *[2]Department of Materials Science and Engineering, Korea University*
TB1-C-5 **10:15-10:30**	***Ab initio* Approach on the Anisotropic Growth of GaAs: from DFT to Growth Kinetics** In Won Yeu[1], Gyuseung Han[1,2,3], Cheol Seong Hwang[2,3], and Jung-Hae Choi[1] *[1]Electronic Materials Research Center, KIST, [2]Department of Materials Science and Engineering, Seoul National University, [3]Inter-University Semiconductor Research Center, Seoul National University*